

HiPerFRED<sup>2</sup>

# DPF80C200HB

preliminary

 $V_{RRM} = 200 V$ 

 $I_{FAV} = 2x \quad 40 A$ 

 $t_{rr} = 55 \, \text{ns}$ 

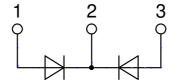
High Performance Fast Recovery Diode Low Loss and Soft Recovery Common Cathode

Part number

#### DPF80C200HB



Backside: cathode



#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

#### **Applications:**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

#### Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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<b>Fast Dio</b>	de			1	Ratings	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse blockii	ng voltage	$T_{VJ} = 25^{\circ}C$			200	V
V <sub>RRM</sub>	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			200	V
IR	reverse current, drain current	$V_R = 200 \text{ V}$	$T_{VJ} = 25^{\circ}C$			1	μΑ
		$V_R = 200 V$	$T_{VJ} = 150$ °C			0.2	mΑ
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 40 A	$T_{VJ} = 25^{\circ}C$			1.22	V
		$I_F = 80 \text{ A}$				1.45	٧
		I <sub>F</sub> = 40 A	T <sub>vJ</sub> = 150°C			0.95	٧
		$I_F = 80 \text{ A}$				1.20	٧
I <sub>FAV</sub>	average forward current	T <sub>C</sub> = 145°C	T <sub>vJ</sub> = 175°C			40	Α
		rectangular d = 0.5					1 1 1 1
V <sub>F0</sub>	threshold voltage		$T_{VJ} = 175$ °C			0.67	٧
r <sub>F</sub>	slope resistance	ss calculation only				5.8	mΩ
R <sub>thJC</sub>	thermal resistance junction to case	)				0.7	K/W
R <sub>thCH</sub>	thermal resistance case to heatsin	k			0.3		K/W
P <sub>tot</sub>	total power dissipation		$T_{C} = 25^{\circ}C$			215	W
I <sub>FSM</sub>	max. forward surge current	$t = 10 \text{ ms}$ ; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			560	Α
CJ	junction capacitance	$V_R = 100  \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		81		pF
I <sub>RM</sub>	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		6		Α
		$I_F = 40 \text{ A}; V_R = 100 \text{ V}$	$T_{VJ} = 125 ^{\circ}\text{C}$		11		Α
t <sub>rr</sub>	reverse recovery time	$I_F = 40 \text{ A}; V_R = 100 \text{ V}$ -di <sub>F</sub> /dt = 200 A/\text{\mu}s	$T_{VJ} = 25 ^{\circ}C$		55		ns
	)		$T_{VJ} = 125 ^{\circ}\text{C}$		85		ns

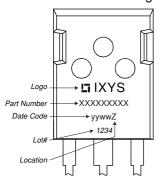


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Package	Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I <sub>RMS</sub>	RMS current	per terminal 1)			70	Α	
T <sub>VJ</sub>	virtual junction temperature		-55		175	°C	
Top	operation temperature		-55		150	°C	
T <sub>stg</sub>	storage temperature		-55		150	°C	
Weight				6		g	
M <sub>D</sub>	mounting torque		0.8		1.2	Nm	
F <sub>c</sub>	mounting force with clip		20		120	N	

## **Product Marking**



#### Part description

D = Diode

P = HiPerFRED

F = ultra fast

80 = Current Rating [A]

C = Common Cathode

200 = Reverse Voltage [V] HB = TO-247AD (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPF80C200HB	DPF80C200HB	Tube	30	508214

Similar Part	Package	Voltage class
DPF60C200HJ	ISOPLUS247 (3)	200

<b>Equivalent Circuits for Simulation</b>			* on die level	$T_{VJ} = 175^{\circ}C$
$I \rightarrow V_0$		Fast Diode		
V <sub>0 max</sub>	threshold voltage	0.67		V
$R_{0 \text{ max}}$	slope resistance *	3.2		$m\Omega$

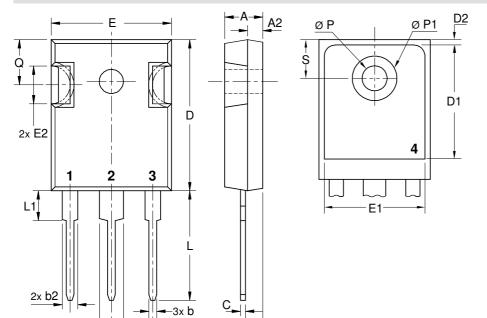




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### Outlines TO-247

2xe



Sym.	Inches		Millim	eter
	min.	max.	min.	max.
Α	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
е	0.215	BSC	5.46	BSC
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
ØΡ	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242	BSC	6.14	BSC
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
С	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39

